EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	71	effective with insulation adj layer with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 07:22
L5	6	effective with insulation adj layer with thickness same gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:07
L6	1485	(257/288).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:09
L7	392	(257/402).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:10
L8	243	(257/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 08:10
S1	12681	electrode with concentration with impurit$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:20
S2	3552	electrode with concentration adj impurit$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:50
S3	1729	electrode with concentration adj impurit$3 and gate adj insulat$4 with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:51

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S4	980	electrode with concentration adj impurit$3 and gate adj insulat$4 with film with thick$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:52
S5	928	electrode with concentration adj impurit$3 and gate adj insulat$4 with film with thick$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 18:52
S6	16	electrode near concentration adj impurit$3 and gate adj insulat$4 with film with thick$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/06 19:30
S7	17	electrode near concentration near impurit$3 and gate adj insulat$4 with film with thick$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:39
S8	1010	(438/275).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 19:34
S9	0	("008and7").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 19:34
S10	0	S8 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:35
S11	10	S8 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:52

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S12	659	257/392	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:52
S13	15	S12 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/01/06 19:52
S14	118382	polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:21
S15	0	dpoing with gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/07 18:24
S16	7938	doping with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:34
S17	157231	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:32
S18	709	S16 with S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:32
S19	34	S16 with S17 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/09 07:21

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S20	919	doping with concentration with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:37
S21	1	S20 with S17 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:35
S22	3	S20 same S17 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:35
S23	9	doping with concentration with polysilicon with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:37